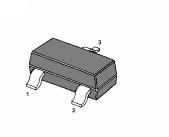
## MMBTSC5084

#### **NPN Silicon Epitaxial Planar Transistor**

for low noise, high gain amplifier at VHF~UHF band.

The transistor is subdivided into two groups O and Y, according to its DC current gain.



1. Base 2. Emitter 3. Collector

SOT-23 Plastic Package

### Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

	Symbol	Value	Unit
Collector Base Voltage	V <sub>CBO</sub>	20	V
Collector Emitter Voltage	V <sub>CEO</sub>	12	V
Emitter Base Voltage	$V_{EBO}$	3	V
Base Current	I <sub>B</sub>	40	mA
Collector Current	Ic	80	mA
Power Dissipation	P <sub>tot</sub>	200	mW
Junction Temperature	T <sub>j</sub>	125	°C
Storage Temperature Range	Ts	-55 to +125	°C







# MMBTSC5084

#### Characteristics at T<sub>amb</sub>=25 °C

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at V <sub>CE</sub> =10V, I <sub>C</sub> =20mA					
Current Gain Group O	h <sub>FE</sub>	80	-	160	-
Υ	h <sub>FE</sub>	120	-	240	-
Collector Cutoff Current					
at V <sub>CB</sub> =10V	I <sub>CBO</sub>	-	-	1	μA
Emitter Cutoff Current					
at V <sub>EB</sub> =1.0V	I <sub>EBO</sub>	-	-	1	μA
Transition Frequency					
at V <sub>CE</sub> =10V, I <sub>C</sub> =20mA	$f_{T}$	5	7	-	GHz
Reverse Transfer Capacitance					
at V <sub>CB</sub> =10V, f=1MHz <sup>1)</sup>	$C_{re}$	-	0.65	1.15	pF
Output Capacitance					
at V <sub>CB</sub> =10V, f=1MHz <sup>1)</sup>	$C_ob$	-	1	-	pF
Insertion Gain					
at V <sub>CE</sub> =10V, I <sub>C</sub> =20mA, f=500MHz	$\left  S_{21e} \right ^2_1$	-	16.5	-	dB
Insertion Gain					
at V <sub>CE</sub> =10V, I <sub>C</sub> =20mA, f=1.0GHz	$\left  S_{21e} \right _{2}^{2}$	7.5	11	-	dB
Noise Figure					
at V <sub>CE</sub> =10V, I <sub>C</sub> =5mA, f=500MHz	$NF_1$	-	1	-	dB
Noise Figure					
at $V_{CE}$ =10V, $I_{C}$ =5mA, f=1.0GHz	$NF_2$		1.1	2	dB

 $<sup>^{1)}</sup>$   $C_{\text{re}}\!$  is measured by 3 terminal method with capacitance bridge.





